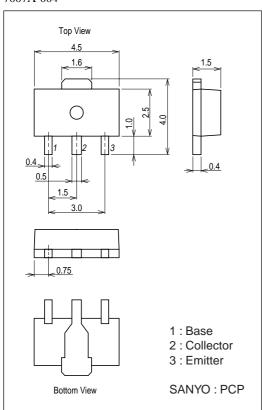
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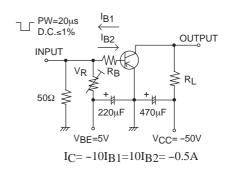
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Collector-to-Emitter Saturation Voltage	VCE(sat)	IC=-1A, IB=-100mA		-120	-240	mV
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	I _C =-1A, I _B =-100mA		-0.85	-1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	IC=-10μA, IE=0A	-100			V
Collector-to-Emitter Breakdown Voltage	V(BR)CES	IC=-100μA, RBE=0Ω	-100			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=-1mA, RBE=∞	-100			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	IE=-10μA, IC=0A	-7			V
Turn-ON Time	ton	See specified Test Circuit.		40		ns
Storage Time	t _{stg}	See specified Test Circuit.		600		ns
Fall Time	tf	See specified Test Circuit.		30		ns

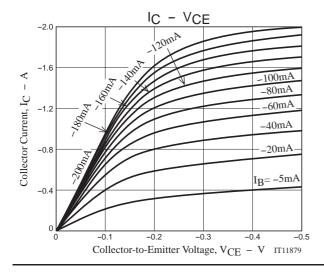
Package Dimensions

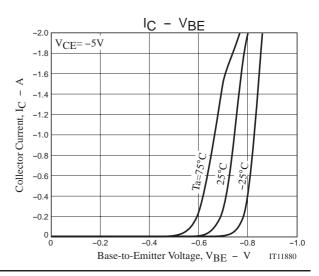
unit : mm (typ) 7007A-004

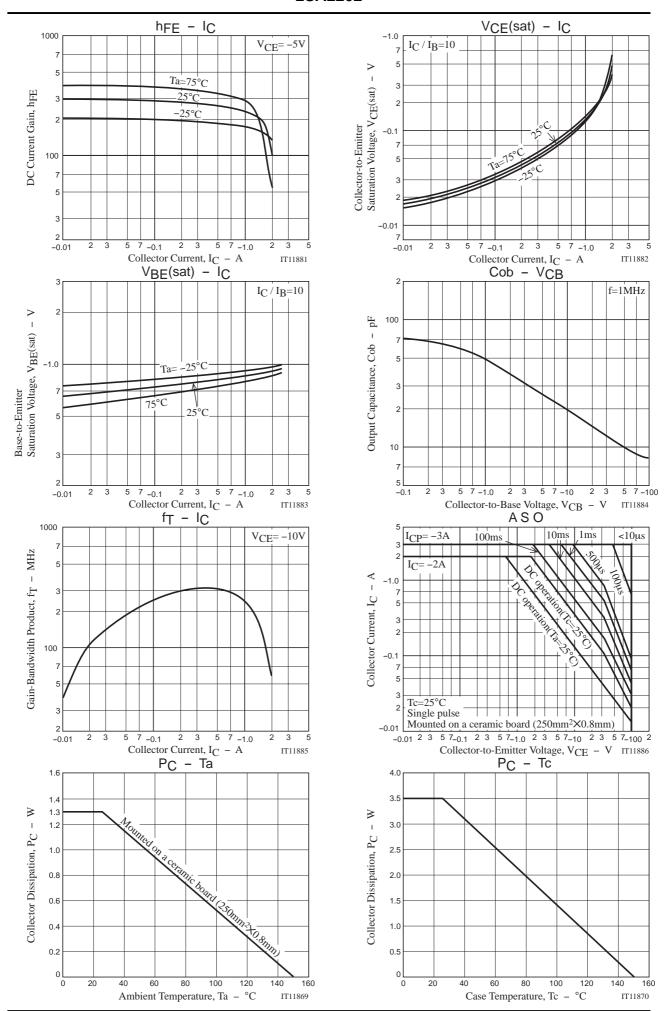


Switching Time Test Circuit









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